

RGTH00TS65

650V 50A Field Stop Trench IGBT

V_{CES}	650V
I _{C(100°C)}	50A
V _{CE(sat) (Typ.)}	1.6V
P_D	277W

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

Applications

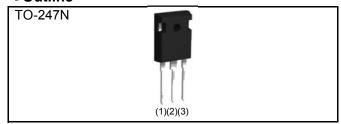
PFC

UPS

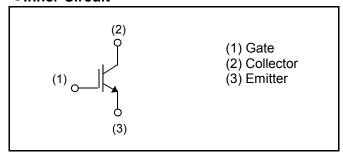
Power Conditioner

ΙH

Outline



●Inner Circuit



Packaging Specifications

	Packaging	Tube	
	Reel Size (mm)	-	
Typo	Tape Width (mm)	-	
Туре	Basic Ordering Unit (pcs)	450	
	Packing code	C11	
	Marking	RGTH00TS65	

● Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V_{CES}	650	V
Gate - Emitter Voltage		V_{GES}	±30	V
Collector Current	T _C = 25°C	I _C	85	А
	T _C = 100°C	I _C	50	А
Pulsed Collector Current		I _{CP} *1	200	А
Dawar Dissipation	T _C = 25°C	P_{D}	277	W
Power Dissipation	T _C = 100°C	P_{D}	138	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

^{*1} Pulse width limited by T_{imax.}

●Thermal Resistance

Parameter	Symbol	Values			Unit
raiametei		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.54	°C/W

ullet IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
r ai ai i i e te i	Symbol		Min.	Тур.	Max.	Offic
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{C} = 10 \mu A, V_{GE} = 0 V$	650	1	ı	V
Collector Cut - off Current	I _{CES}	V _{CE} = 650V, V _{GE} = 0V	1	1	10	μΑ
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	1	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 34.7 \text{mA}$	4.5	5.5	6.5	V
		I _C = 50A, V _{GE} = 15V				
Collector - Emitter Saturation Voltage	$V_{CE(sat)}$	T _j = 25°C	-	1.6	2.1	V
		T _j = 175°C	-	2.1	-	

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Darameter	Symbol	Conditions	Values			Linit
Parameter			Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V	-	2740	-	
Output Capacitance	C _{oes}	V _{GE} = 0V	-	106	-	pF
Reverse Transfer Capacitance	C _{res}	f = 1MHz	-	43	-	
Total Gate Charge	Q_g	V _{CE} = 300V	-	94	-	
Gate - Emitter Charge	Q_{ge}	I _C = 50A	-	22	-	nC
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	31	-	
Turn - on Delay Time	t _{d(on)}	I _C = 50A, V _{CC} = 400V	-	39	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	63	-	
Turn - off Delay Time	$t_{d(off)}$	T _j = 25°C	-	143	-	ns
Fall Time	t _f	Inductive Load	-	50	-	
Turn - on Delay Time	t _{d(on)}	I _C = 50A, V _{CC} = 400V	-	39	-	
Rise Time	t _r	$V_{GE} = 15V, R_G = 10\Omega$	-	63	-	20
Turn - off Delay Time	t _{d(off)}	T _j = 175°C	-	159	-	ns
Fall Time	t _f	Inductive Load	-	62	-	
		I _C = 200A, V _{CC} = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FU	FULL SQUARE		
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

• Electrical Characteristic Curves

Fig.1 Power Dissipation vs. Case Temperature

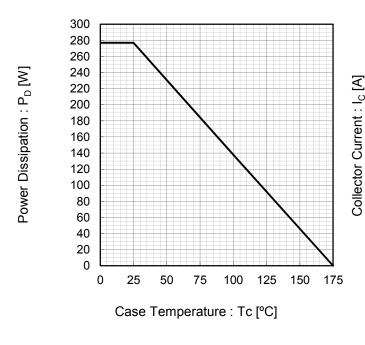
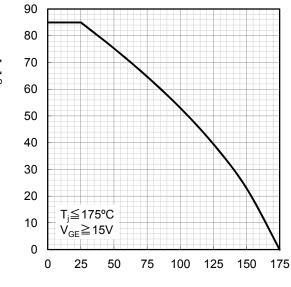


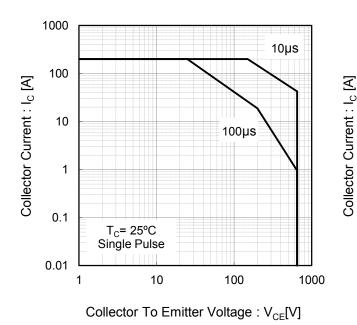
Fig.2 Collector Current vs. Case Temperature



Case Temperature : Tc [°C]

Fig.4 Reverse Bias Safe Operating Area

Fig.3 Forward Bias Safe Operating Area



220 200 180 160 140 120

240

100 80 60 40 T_i≦175°C 20 0 200 400 600 800

Collector To Emitter Voltage : $V_{CE}[V]$

Electrical Characteristic Curves

Fig.5 Typical Output Characteristics

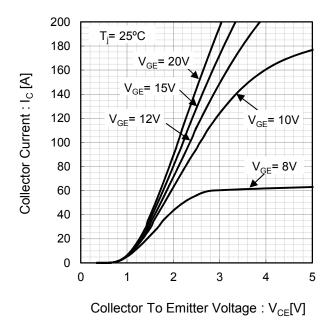
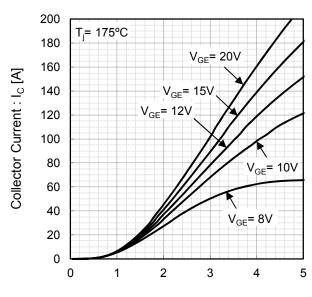


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V_{CE}[V]

Fig.7 Typical Transfer Characteristics

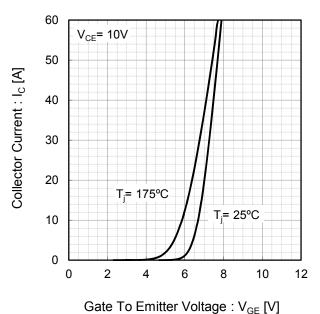
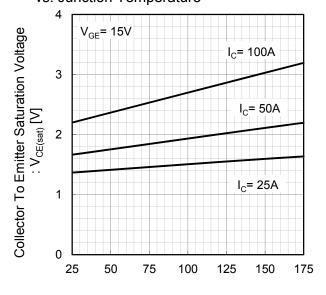


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T_i [°C]

Electrical Characteristic Curves

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

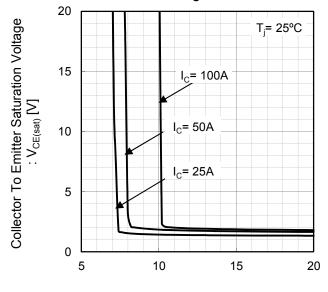
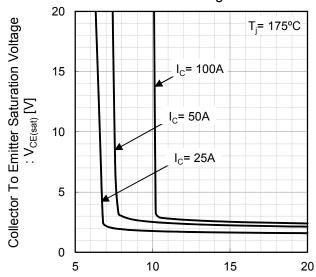


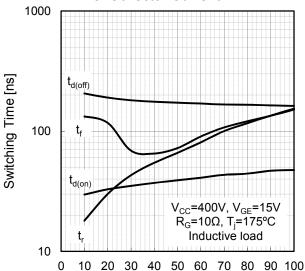
Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : $V_{GE}[V]$

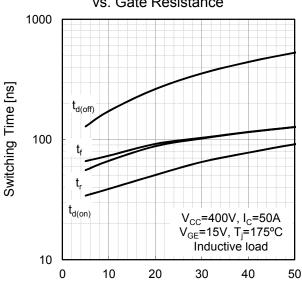
Gate To Emitter Voltage : V_{GE} [V]

Fig.11 Typical Switching Time vs. Collector Current



Collector Current : I_C [A]

Fig.12 Typical Switching Time vs. Gate Resistance



Gate Resistance : $R_G[\Omega]$

• Electrical Characteristic Curves

Fig.13 Typical Switching Energy Losses vs. Collector Current

10 E_{off} 0.1 E_{off} $V_{CC}=400V, V_{GE}=15V$ $E_{G}=10\Omega, T_{J}=175^{\circ}C$ Inductive load

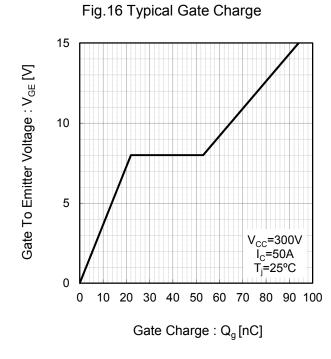
0 10 20 30 40 50 60 70 80 90 100

Collector Current : I_{C} [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ] $\mathsf{E}_{\mathsf{off}}$ 1 0.1 V_{CC}=400V, I_C=50A V_{GE}=15V, T_j=175°C Inductive load 0.01 10 20 0 30 40 50 Gate Resistance : $R_G[\Omega]$

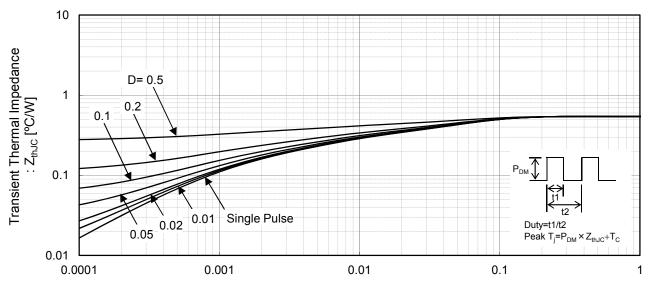
Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz $V_{GE}=0V$ T_i=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE}[V]



•Electrical Characteristic Curves

Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

●Inductive Load Switching Circuit and Waveform

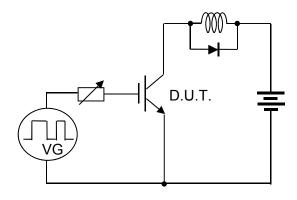


Fig.18 Inductive Load Circuit

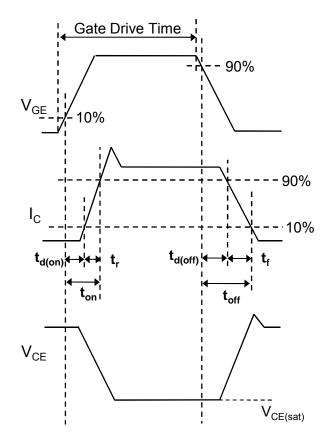


Fig.19 Inductive Load Waveform

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